

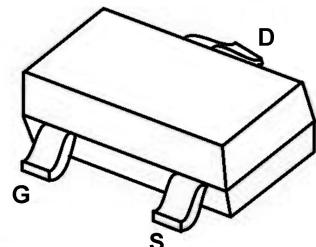
# KY2004K

20V P-Channel Mosfet

## FEATURES

- $R_{DS(ON)} \leq 520m\Omega$  ( 380m $\Omega$  Typ.) @ $V_{GS}=-4.5V$
- $R_{DS(ON)} \leq 700m\Omega$  ( 480m $\Omega$  Typ.) @ $V_{GS}=-2.5V$
- $R_{DS(ON)} \leq 1000m\Omega$  ( 600m $\Omega$  Typ.) @ $V_{GS}=-1.8V$

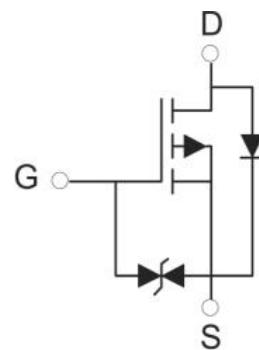
## SOT-23



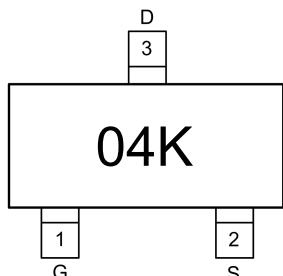
## APPLICATIONS

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics

## P-CHANNEL MOSFET



## MARKING



## MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

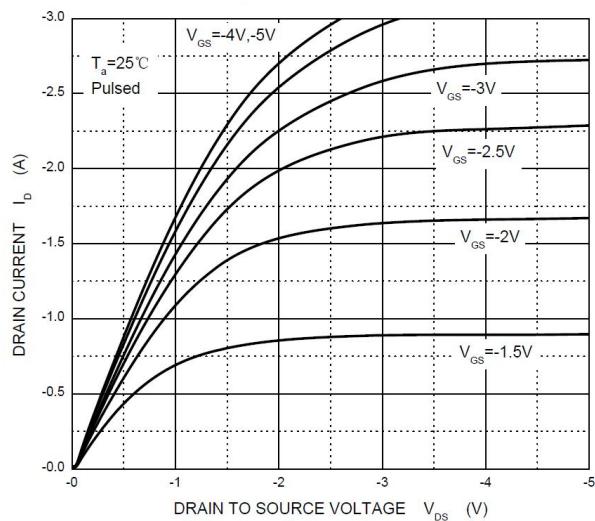
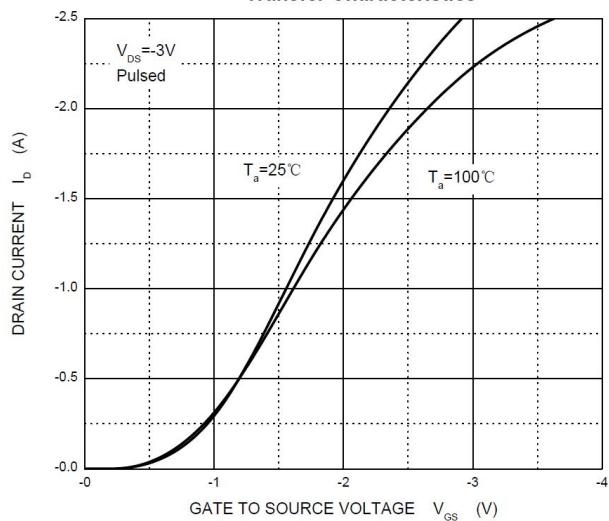
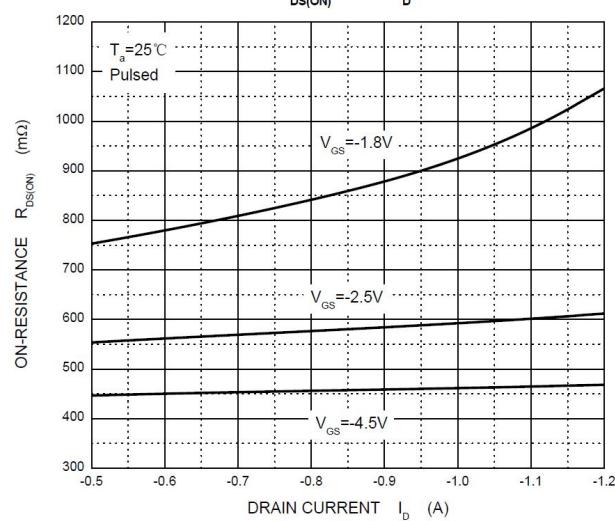
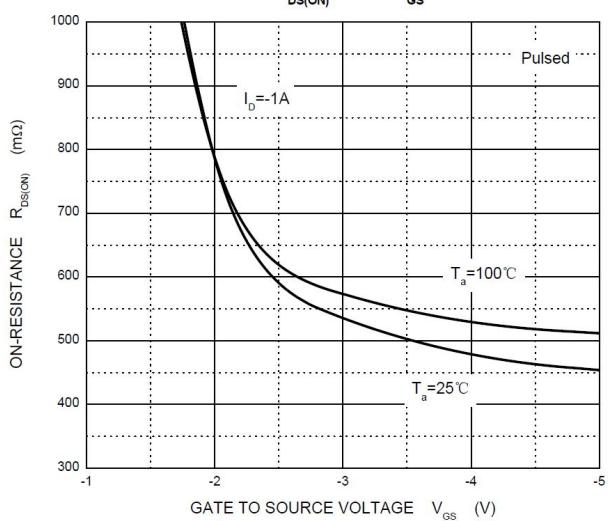
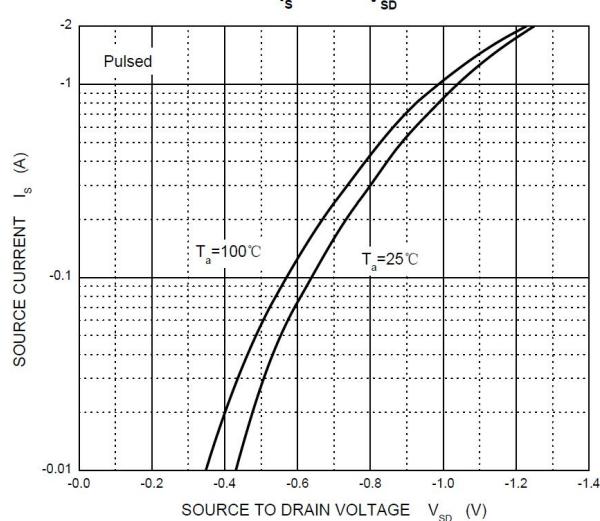
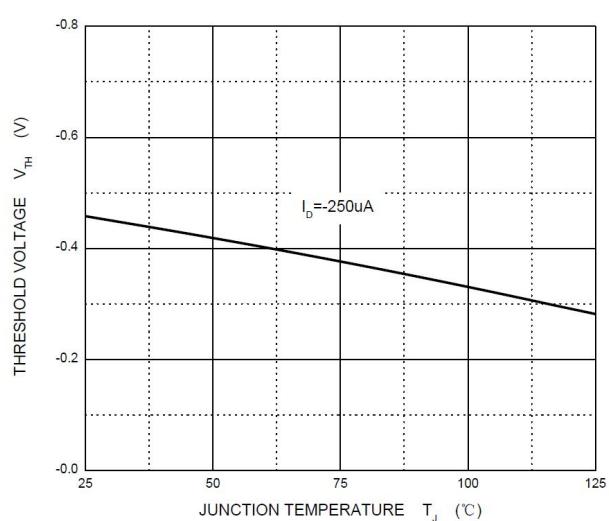
| Symbol          | Parameter                                   | Value     | Unit |
|-----------------|---|-----------|------|
| $V_{DS}$        | Drain-Source Voltage                        | -20       | V    |
| $V_{GS}$        | Gate-Source Voltage                         | $\pm 10$  | V    |
| $I_D$           | Continuous Drain Current                    | -0.66     | A    |
| $I_{DM}$        | Pulsed Drain Current                        | -1.2      | A    |
| $P_D$           | Power Dissipation                           | 0.35      | W    |
| $R_{\theta JA}$ | Thermal Resistance from Junction to Ambient | 417       | °C/W |
| $T_J$           | Junction Temperature                        | 150       | °C   |
| $T_{STG}$       | Storage Temperature                         | -55~ +150 | °C   |

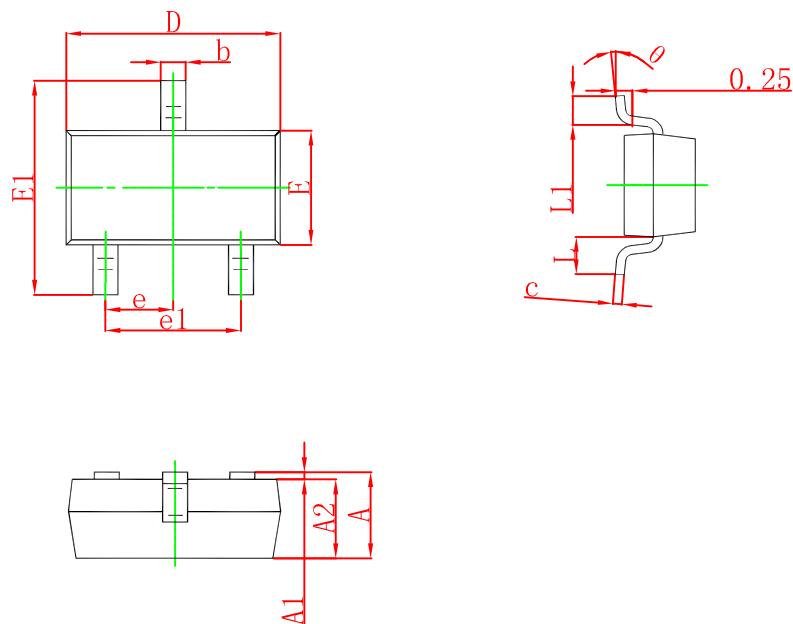
**MOSFET ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified**

| Symbol  | Parameter   | Test Condition  | Min.  | Typ.  | Max. | Units |
|---|---|---|-------|-------|------|-------|
| <b>Off Characteristic</b>                                     |   |   |       |       |      |       |
| V <sub>(BR)DSS</sub>  | Drain-Source Breakdown Voltage                        | V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA   | -20   | -     | -    | V     |
| I <sub>DSS</sub>  | Zero Gate Voltage Drain Current                       | V <sub>DS</sub> = -20V,<br>V <sub>GS</sub> = 0V, T <sub>J</sub> = 25°C                          | -     | -     | -1   | μA    |
| I <sub>GSS</sub>  | Gate to Body Leakage Current                          | V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V  | -     | -     | ±10  | uA    |
| <b>On Characteristics</b>                                     |   |   |       |       |      |       |
| V <sub>GS(th)</sub>   | Gate Threshold Voltage                                | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250μA                                      | -0.35 | -0.65 | -1   | V     |
| R <sub>DS(on)</sub>   | Static Drain-Source<br>On-Resistance <sup>note1</sup> | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -0.5A   | -     | 380   | 520  | mΩ    |
|   |   | V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -0.2A   | -     | 480   | 700  |       |
|   |   | V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -0.1A   | -     | 600   | 1000 |       |
| <b>Dynamic Characteristics</b> <sup>note2</sup>               |   |   |       |       |      |       |
| C <sub>iss</sub>  | Input Capacitance                                     | V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V<br>f = 1.0MHz                                      | -     | 113   | -    | pF    |
| C <sub>oss</sub>  | Output Capacitance                                    |   | -     | 15    | -    | pF    |
| C <sub>rss</sub>  | Reverse Transfer Capacitance                          |   | -     | 9     | -    | pF    |
| <b>Switching Characteristics</b> <sup>note2</sup>             |   |   |       |       |      |       |
| t <sub>d(on)</sub>  | Turn-On Delay Time                                    | V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V<br>R <sub>G</sub> = 10Ω, I <sub>D</sub> = -0.2A | -     | 9     | -    | ns    |
| t <sub>r</sub>  | Turn-On Rise Time                                     |   | -     | 5.7   | -    | ns    |
| t <sub>d(off)</sub>   | Turn-Off Delay Time                                   |   | -     | 32.6  | -    | ns    |
| t <sub>f</sub>  | Turn-Off Fall Time                                    |   | -     | 20.3  | -    | ns    |
| <b>Drain-Source Diode Characteristics and Maximum Ratings</b> |   |   |       |       |      |       |
| V <sub>SD</sub>   | Drain to Source Diode Forward<br>Voltage              | V <sub>GS</sub> = 0V, I <sub>SD</sub> = -0.5A<br>T <sub>J</sub> = 25°C                          | -     | -     | -1.2 | V     |

Notes: 1. Pulse Test: Pulse width < 300μs, Duty Cycle ≤ 2%

2. Guaranteed by design, not subject to production testing

**KY2004K**
**TYPICAL PERFORMANCE CHARACTERISTICS**
**Output Characteristics**

**Transfer Characteristics**

 **$R_{DS(ON)}$  —  $I_D$** 

 **$R_{DS(ON)}$  —  $V_{GS}$** 

 **$I_s$  —  $V_{SD}$** 

**Threshold Voltage**


**KY2004K****SOT-23 PACKAGE OUTLINE DRAWING**

| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 0.900                     | 1.150 | 0.035                | 0.045 |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2     | 0.900                     | 1.050 | 0.035                | 0.041 |
| b      | 0.300                     | 0.500 | 0.012                | 0.020 |
| c      | 0.080                     | 0.150 | 0.003                | 0.006 |
| D      | 2.800                     | 3.000 | 0.110                | 0.118 |
| E      | 1.200                     | 1.400 | 0.047                | 0.055 |
| E1     | 2.250                     | 2.550 | 0.089                | 0.100 |
| e      | 0.950 TYP                 |       | 0.037 TYP            |       |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079 |
| L      | 0.550 REF                 |       | 0.022 REF            |       |
| L1     | 0.300                     | 0.500 | 0.012                | 0.020 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |

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